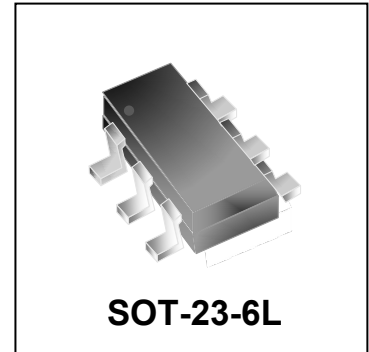


Features

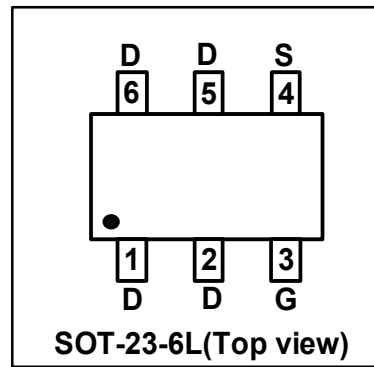
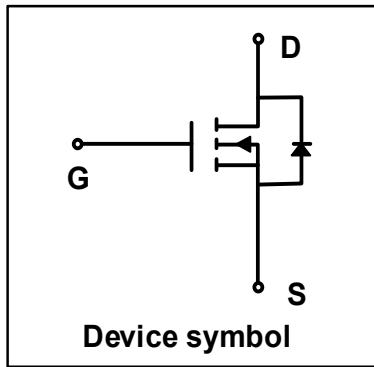
- Way-on Small Signal MOSFETs
- $V_{DS} = 100V$, $I_D = 3.5A$
 $R_{DS(on)} < 100m\Omega @ V_{GS} = 10V$
 $R_{DS(on)} < 120m\Omega @ V_{GS} = 4.5V$
- Trench LV MOSFET Technology

Mechanical Characteristics

- SOT-23-6L Package
- Marking : Making Code
- RoHS Compliant



Schematic & PIN Configuration



Absolute Maximum Rating ($T_A=25^\circ C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	3.5	A
Pulsed Drain Current ¹	I_{DM}	14	A
Power Dissipation	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	62.5	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Gate-Source Leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
Gate-Source Threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	-	2.5	V
Drain-Source on-State Resistance ³	$R_{DS(on)}$	$V_{GS}=10V, I_D=3.5A$	-	78	100	m Ω
		$V_{GS}=4.5V, I_D=2.5A$	-	92	120	
Dynamic Characteristics⁴						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=50V,$ $f=1MHz$	-	1150	-	pF
Output Capacitance	C_{oss}		-	32	-	
Reverse Transfer Capacitance	C_{rss}		-	26	-	
Switching Characteristics⁴						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=50V,$ $I_D=3.5A$	-	21	-	nC
Gate-Source Charge	Q_{gs}		-	3.7	-	
Gate-Drain Charge	Q_{gd}		-	3.6	-	
Turn-on Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DD}=50V,$ $I_D=3.5A, R_G=3\Omega$	-	5.8	-	ns
Rise Time	t_r		-	16	-	
Turn-off Delay time	$t_{d(off)}$		-	18.4	-	
Fall Time	t_f		-	7.2	-	
Source-Drain Body Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$I_S=3.5A, V_{GS}=0V$	-	-	1.2	V
Continuous Source Current	I_S		-	-	3.5	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

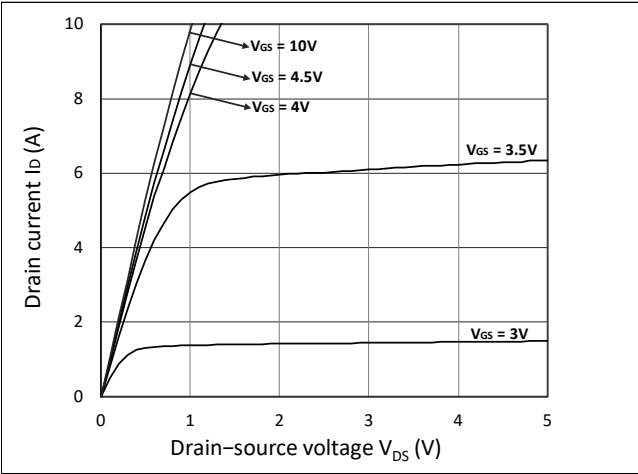


Figure 1. Output Characteristics

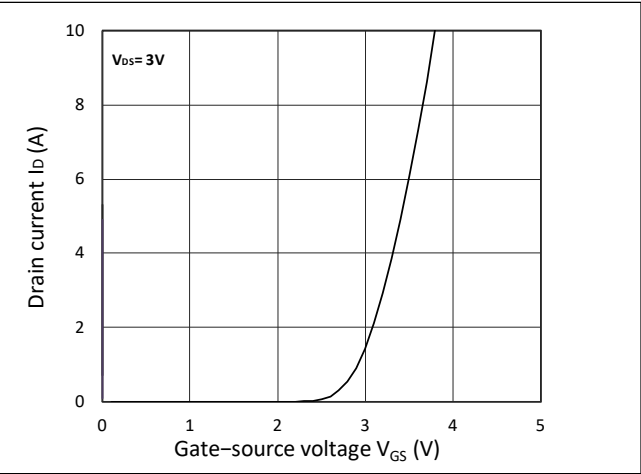


Figure 2. Transfer Characteristics

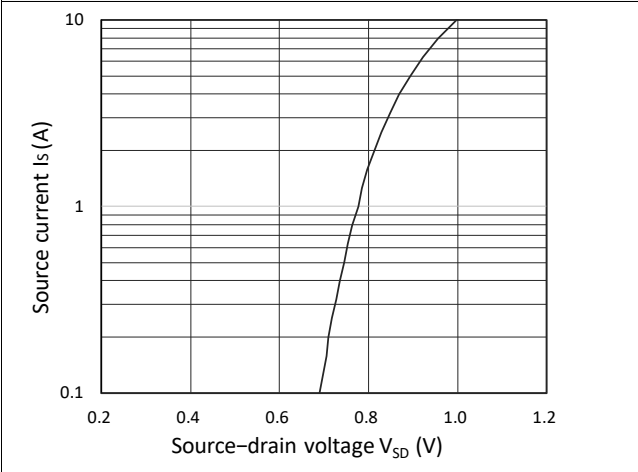


Figure 3. Forward Characteristics of Reverse

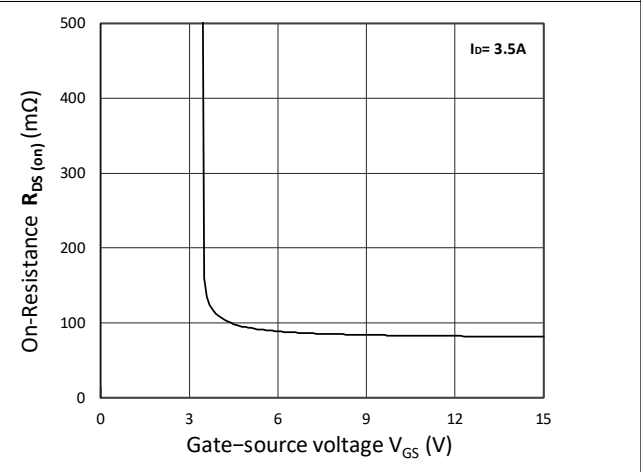


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

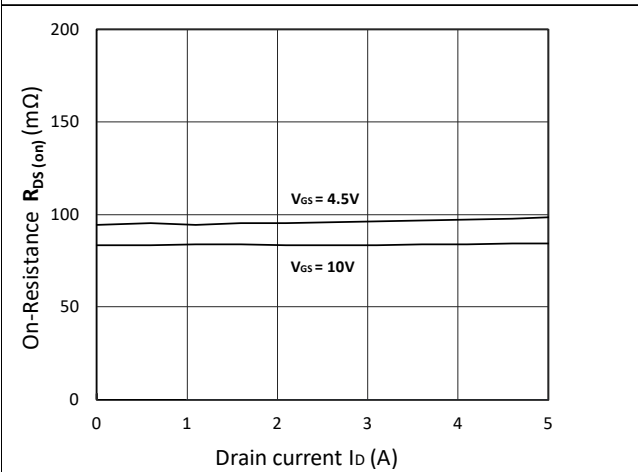


Figure 5. $R_{DS(ON)}$ vs. I_D

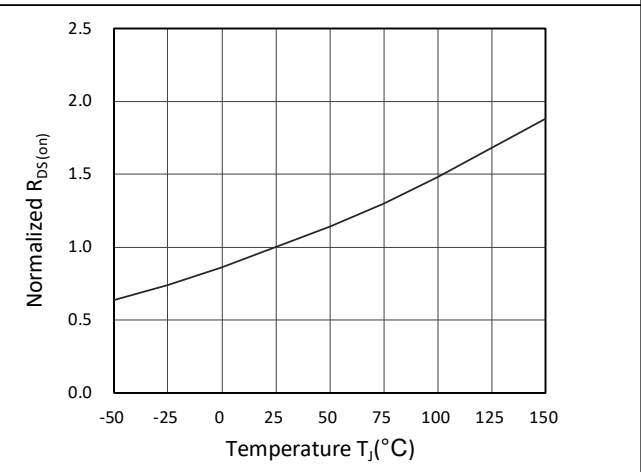


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

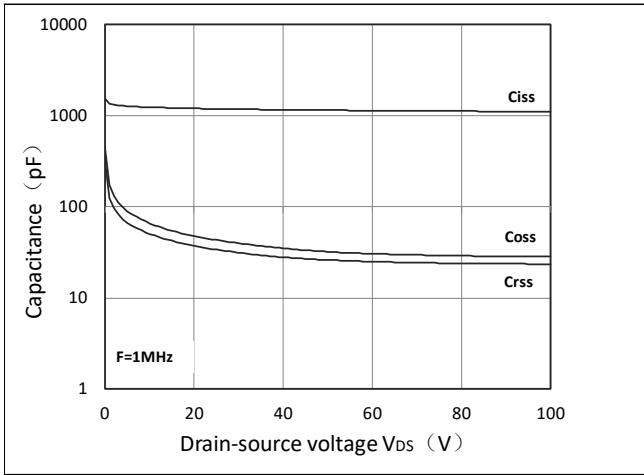


Figure 7. Capacitance Characteristics

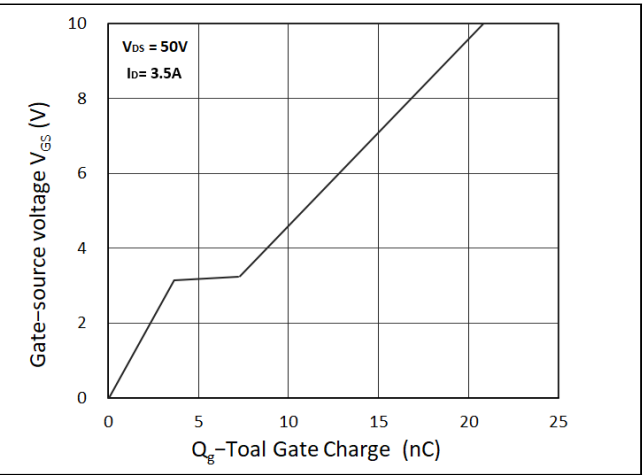


Figure 8. Gate Charge Characteristics

Outline Drawing – SOT-23-6L

PACKAGE OUTLINE

SOT-23-6L

SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.45	0.035	0.057
A1	0.00	0.15	0.000	0.006
b	0.25	0.55	0.010	0.022
c	0.08	0.22	0.003	0.009
D	2.80	3.10	0.110	0.122
E1	1.50	1.75	0.060	0.069
E	2.60	3.00	0.102	0.118
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
L1	0.55	0.75	0.022	0.030
θ1	0°	8°	0°	8°

DIMENSIONS		
DIM	INCHES	MILLIMETERS
C	0.098	2.50
G	0.055	1.40
P	0.037	0.95
X	0.024	0.60
Y	0.043	1.10
Z	0.141	3.60

Notes:

Controlling Dimension: Millimeter.

Marking Codes

Part Number	WM10N35M3
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

No.1001, Shiwan (7) Road, Pudong District, Shanghai, P.R.China.201207

Tel: 86-21-68969993 Fax: 86-21-50757680 Email: market@way-on.com

WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.